

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	248	(DARC ARC (antireflection antireflective anti adj (reflection reflective)) adj (layer film coating)) and gate adj (oxide dielectric) and photoresist and (SiON SiNO silicon adj (oxynitride oxime) "SiNO:H" "SiON:H") and (SiN silicon adj nitride) and (anneal annealed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L2	33	L1 and (@ad<"19980903" @rlad<"19980903")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L3	500	(DARC BARC (antireflection antireflective anti adj (reflection reflective)) adj (layer film coating)) and gate adj (oxide dielectric) and photoresist and (SiON SiNO silicon adj (oxynitride oxime) "SiNO:H" "SiON:H") and (SiN silicon adj nitride) and silicide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L4	63	L3 and (@ad<"19980903" @rlad<"19980903")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L5	42	L4 not L2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L6	11	("6541164").URPN.	USPAT	OR	ON	2007/03/13 12:35
L7	381	anneal\$2 with silicide with (inert nitrogen "N.sub.2")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L8	209	L7 and (@ad<"19980903" @rlad<"19980903")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L9	158	L8 and (MOSFET gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/13 12:35
L10	555	(257/E29.156).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/13 12:35
L11	564	(257/413).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/13 12:35